REMARKS

At the outset, Applicant wishes to thank the Examiner for the courtesies extended to the Applicant's representatives during the personal interview conducted on January 26, 2005. The final Office Action of November 5, 2004 has been received and contents carefully reviewed.

By this Amendment, Applicant amends the specification and claims 1 and 11. No new matter is added to the specification. In addition, Applicant cancels claims 21-24 without prejudice or disclaimer. Accordingly, claims 1, 3-7, 9-11 and 13-20 are currently pending in the present application. Reexamination and reconsideration of the application are respectfully requested.

In the Office Action, the Examiner rejected claims rejected claim 23 under 35 U.S.C. § 102(b) as being anticipated by Applicant's Related Art ("ARA"), and rejected claims 1, 3-7, 9-11 and 13-20 under 35 U.S.C. § 103(a) as being unpatentable over ARA in view of Taniguchi et al. (JP 2-58030A). Applicant respectfully traverses these rejections.

Claim 1 is allowable over the cited references in that claim 1 recites a combination of elements including, for example, "...wherein an entire area of the "ㄷ"-shaped channel is formed over the gate electrode, the gate electrode underlies a part of the data line, the source electrodes and a part of the drain electrode so that the "ㄷ"-shaped channel is formed at parts of the source and drain electrodes facing the protrusion, the entirety of the protrusions of the source and drain electrodes is formed within the area of the semiconductor layer, and the protrusion of the source electrode is parallel to and offset from the protrusion of the drain electrode." None of the cited references, singly or in combination, teaches or suggests at least this feature of the claimed invention. Accordingly, Applicant respectfully submits that claim 1 and claims 3-7 and 9-10, which depend therefrom, are allowable over the cited references.

In the Office Action on page 5, the Examiner states,

> "Note, because APA forms the entire source/drain electrodes over the semiconductor layer, and because Taniguchi forms plural protrusions over the semiconductor layer to increase the channel width, one of ordinary skill would recognize that the entirety of the protrusions formed in Taniguchi should be formed entirely over the semiconductor layer in order to further increase the channel width, as taught to be beneficial by Taniguchi. Further, in this

> regard, nowhere in the instant specification is the feature that the protrusions are formed entirety over the area of the semiconductor layer, discussed or taught to be critical to the instant invention. Therefore it is not considered to have critical value in light of the applied art –especially given that Taniguchi teaches the same benefit as does the instant specification of increased channel width and decreased TFT size."

Applicant respectfully submits that one of the principles of the present invention is to have a compact TFT to increase the aperture ratio without sacrificing the amount of the ON-current of the TFT. See *Present Application*, for example, paragraphs [0036]-[0037]. Accordingly, it is important for a TFT according to the present invention to have such features as "the protrusion of the source electrode extends directly from a data line" and "the entirety of the protrusions of the source and drain electrodes is formed within the area of the semiconductor layer", which are recited in claim 1 and are not disclosed in Taniguchi et al. Applicant further respectfully submits that the motivation to combine the references comes from the present invention and not from Taniguchi et al., which is impermissible.

Claim 11 is allowable over the cited references in that claim 11 recites a combination of elements including, for example, "...wherein an entire area of the "ㄷ"-shaped channel is formed over the gate electrode, the gate electrode underlies a part of the data line, the source electrodes and a part of the drain electrode so that the "ㄷ"-shaped channel is formed at parts of the source and drain electrodes facing the protrusion, the entirety of the protrusions of the source and drain electrodes is formed within the area of the semiconductor layer, and the protrusion of the source electrode is parallel to and offset from the protrusion of the drain electrode." None of the cited references, singly or in combination, teaches or suggests at least this feature of the claimed invention. Accordingly, Applicant respectfully submits that claim 11 and claims 13-20, which depend therefrom, are allowable over the cited references.

Applicant believes the application is in condition for allowance and early, favorable action is respectfully solicited. If the Examiner deems that a telephone conference would further the prosecution of this application, the Examiner is invited to call the undersigned attorney at the telephone number (202) 496-7500. All correspondence should continue to be sent to the below-listed address.

If these papers are not considered timely filed by the Patent and Trademark Office, then a petition is hereby made under 37 C.F.R. §1.136, and any additional fees required under 37 C.F.R. §1.136 for any necessary extension of time, or any other fees required to complete the filing of this response, may be charged to Deposit Account No. 50-0911. Please credit any overpayment to deposit Account No. 50-0911.

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Respectfully submitted,

By _____

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